

ABSTRACT

A method of reducing fluorine contamination on a integrated circuit wafer surface is achieved. The method comprises placing an integrated circuit wafer on a cathode stage. The integrated circuit wafer comprises a surface contaminated with fluorine. The integrated circuit wafer is plasma treated with a plasma comprising a reducing gas that forms HF from the fluorine and a bombardment gas that removes the fluorine from the surface. The cathode stage is heated to thereby increase the rate of the fluorine removal.